ΡΛΝ	ĴΪΤ
	SEMI CONDUCTOR



#### 20V P-Channel Enhancement Mode MOSFET

Current

-4.2A

#### Features

Voltage

• RDS(ON) , VGS@-4.5V, ID@-4.2A<52mΩ

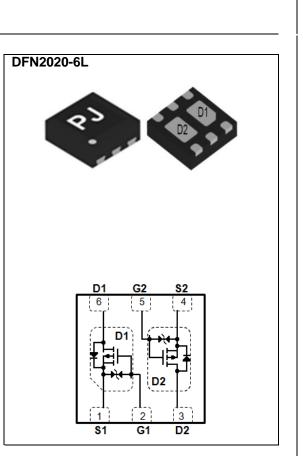
-20 V

- RDS(ON) , VGS@-2.5V, ID@-3.3A<62mΩ
- RDS(ON), VGS@-1.8V, ID@-2.2A<73mΩ</li>
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- ESD Protected
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std.

(Halogen Free)

#### **Mechanical Data**

- Case: DFN2020-6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00032 ounces, 0.0093 grams
- Marking: 815



#### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	-20	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 8	V
Continuous Drain Current		I <sub>D</sub>	-4.2	А
Pulsed Drain Current		I <sub>DM</sub>	-16.8	А
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	1.5	W
	Derate above 25°C		12	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal resistance - Junction to Ambient <sup>(Note 3)</sup>		R <sub>eja</sub>	83.3	°C/W



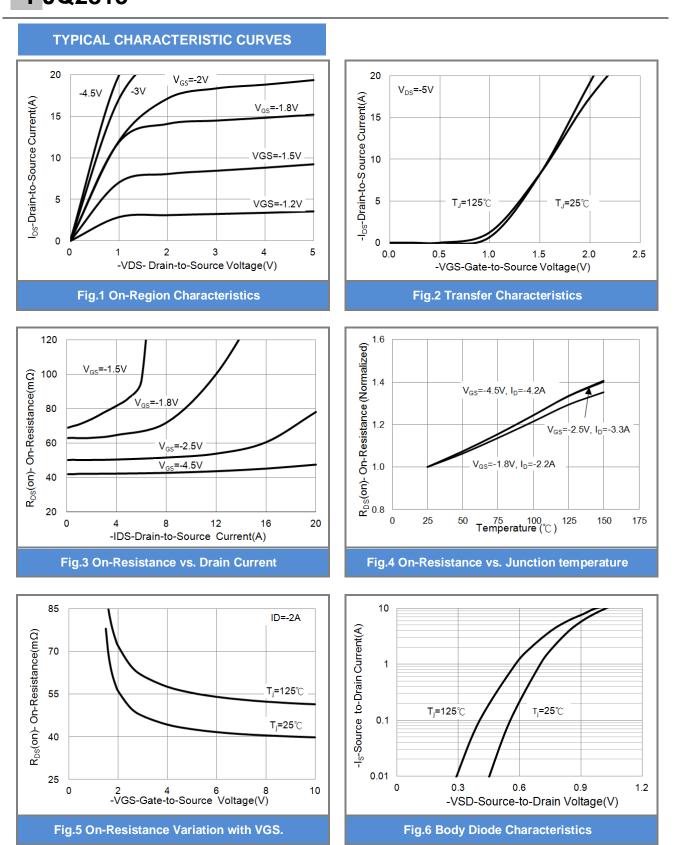
### **Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static					I	
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250$ uA	-0.35	-0.55	-0.9	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-4.2A	-	43	52	mΩ
		V <sub>GS</sub> =-2.5V,I <sub>D</sub> =-3.3A	-	51	62	
		V <sub>GS</sub> =-1.8V,I <sub>D</sub> =-2.2A	-	61	73	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V	-	-0.01	-1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V,V <sub>DS</sub> =0V	-	<u>+</u> 6	<u>+</u> 10	uA
Dynamic (Note 6)						
Total Gate Charge	$Q_{g}$	101/1 4.04	-	24	-	nC
Gate-Source Charge	$Q_gs$	V <sub>DS</sub> =-10V, I <sub>D</sub> =-4.2A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	1.5	-	
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =-4.5V (1000 1,2)	-	2.5	-	
Input Capacitance	Ciss		-	907	-	
Output Capacitance	Coss	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	90	-	pF
Reverse Transfer Capacitance	Crss		-	70	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	45	-	
Turn-On Rise Time	tr	$V_{DD}$ =-10V, I <sub>D</sub> =-4.2A, $V_{GS}$ =-4.5V, $R_{G}$ =6 $\Omega$ <sup>(Note 1.2)</sup>	-	79	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	193	-	ns
Turn-Off Fall Time	tf	K <sub>G</sub> =017	-	826	-	
Drain-Source Diode						
Maximum Continuous Drain-Source				-	-1.5	А
Diode Forward Current	I <sub>S</sub>		-	-	-1.5	A
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	-0.66	-1.2	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 5. Reua is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

### PJQ2815



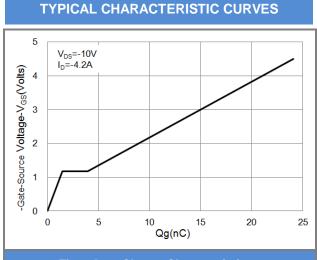


Fig.7 Gate-Charge Characteristics

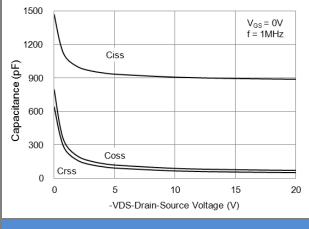


Fig.9 Capacitance vs. Drain-Source Voltage.

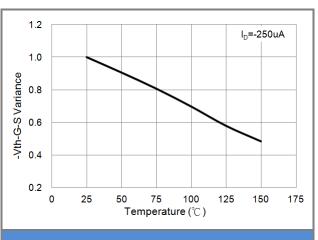


Fig.8 Threshold Voltage Variation with Temperature.

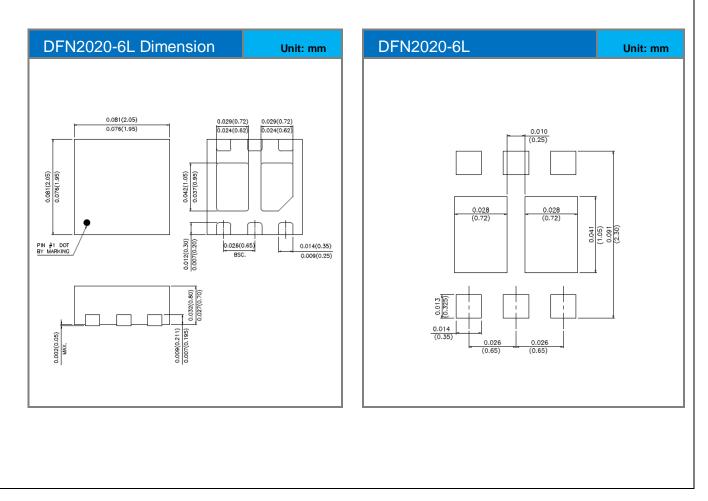




#### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJQ2815_R1_00001	DFN2020-6L	3K pcs / 7" reel	815	Halogen free

#### MOUNTING PAD LAYOUT







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